/ Descriptions

WR0459I ṂṂ Ł QSQ ÆṀ ч s ll ㄱ Silicon NPN transistor in a TO-126F Plastic Package.

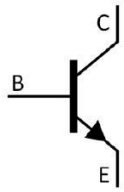
/ Features

Ầ ʜ ゐ ỷ ồ
high speed switching.

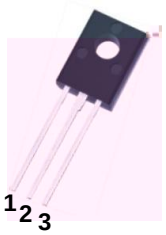
/ Applications

ᵻ ˍ ḭ ı ' ѽ ᶻ ı ス ゐ Ầ ʜ ⌇
Power audio amplifier, high speed switching applications.

/ Equivalent Circuit



/ Pinning



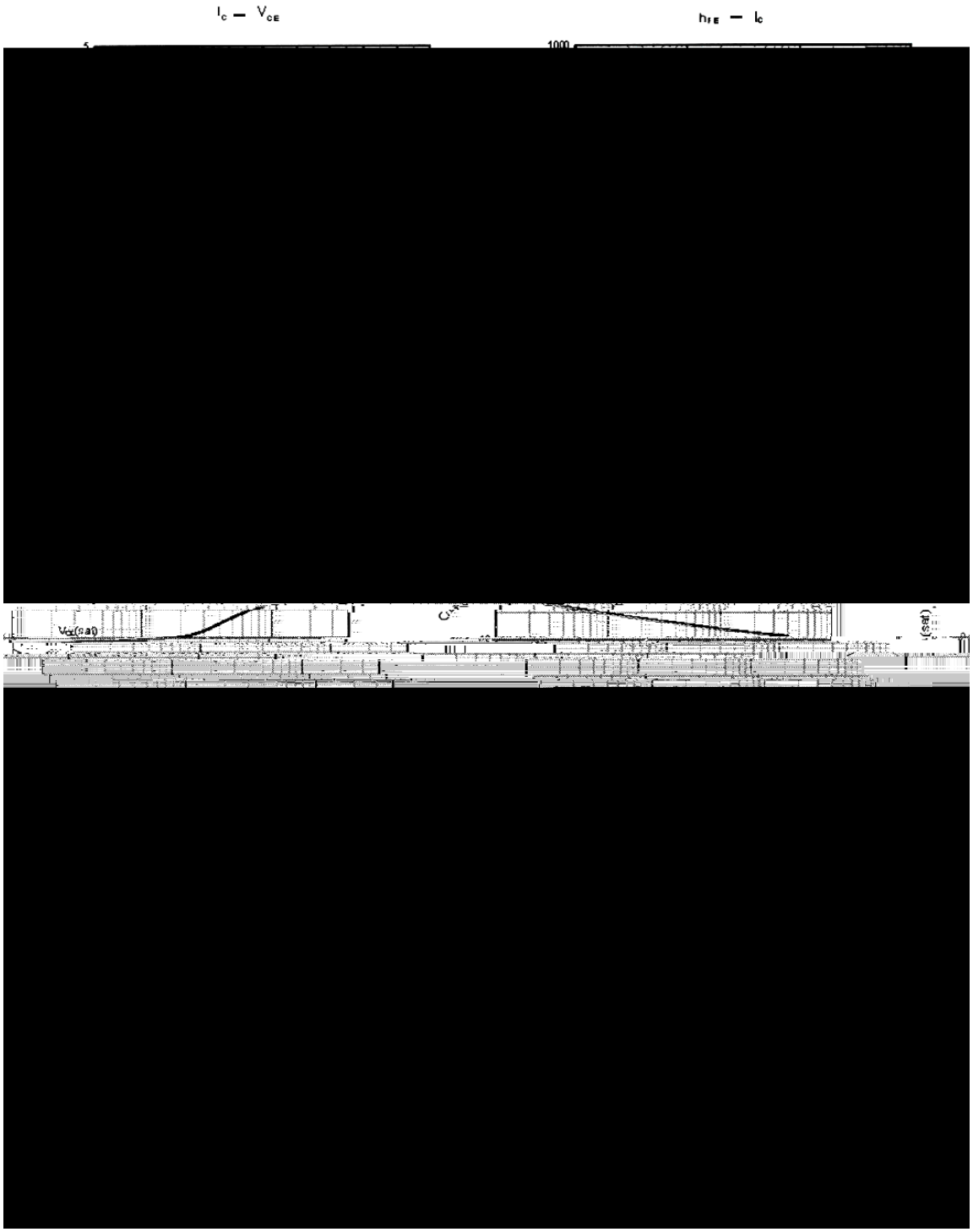
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

/ h_{FE} Classifications & Marking

ỏ ᴍ ヽ ب ˝ See Marking Instructions.

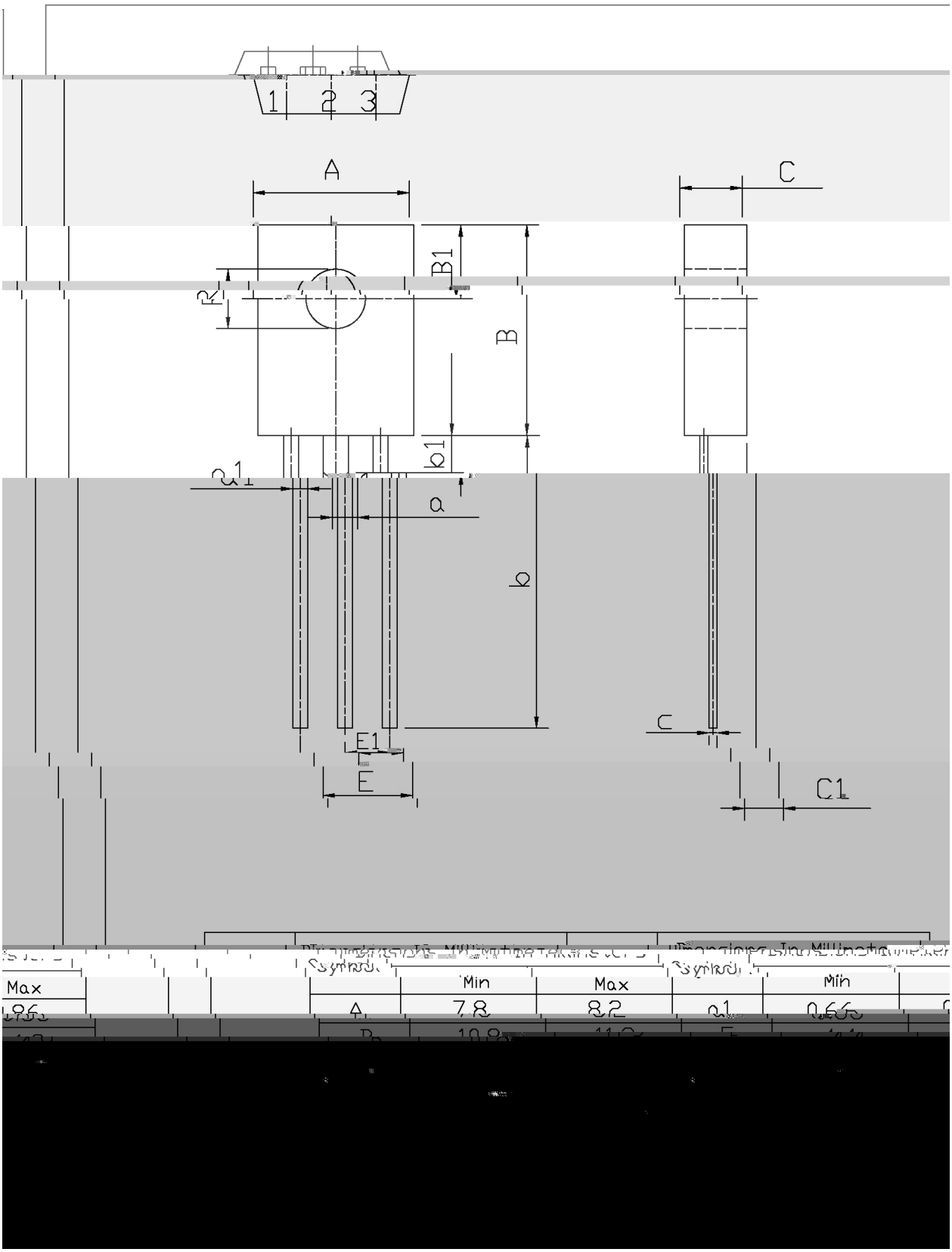
v ‴Ω Parameter	ϒ N Symbol	‴Ω Ö Rating	D Ђ Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current – Continuous	I_C	3.0	A
Collector Current – Continuous(Pulse)	I_{CP}	6.0	A
Base Current – Continuous	I_B	1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	P_C(Tc=25)		

/ Electrical Characteristic Curve



/ Package Dimensions

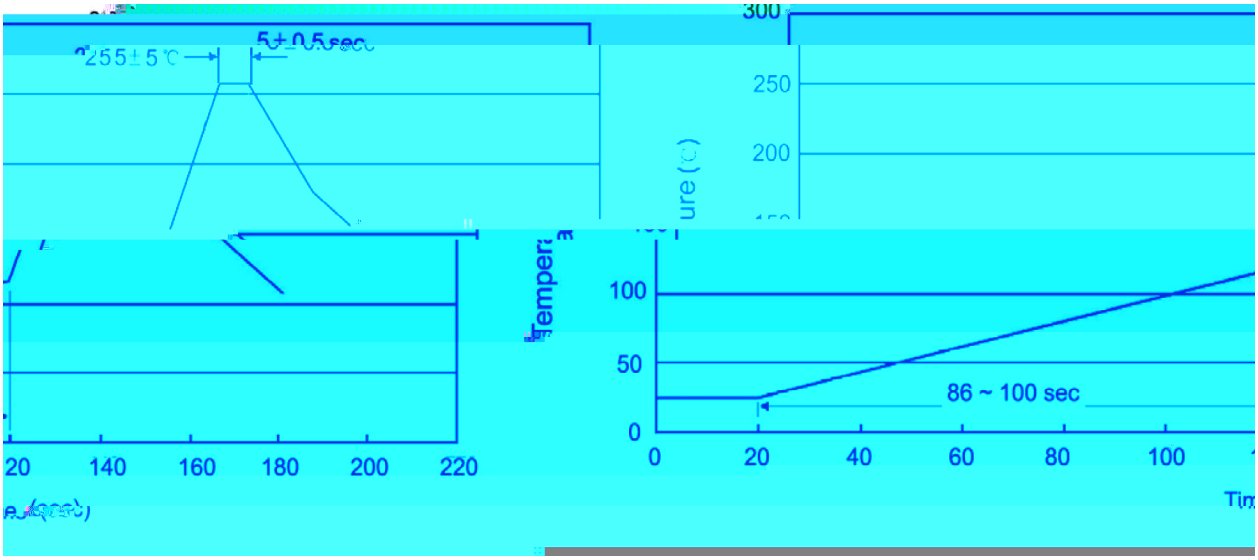
TO-126T 单位：mm



Symbol	Min	Max	Symbol	Min	Max
A	7.8	8.2	a1	0.65	0.85
B	10.8	11.2	E	2.2	2.4

KSE180
Rev.E Mar.-2016

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı ˋH ڑ ˋY ﾊ ㎞ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻉ ỷ ㎞ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ł ˋH ڑ χ 10 ° 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

ˈQ ţ ﾔ Ł / BULK

Package Type	Units					Dimension		(unit mm³)
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

˛ ﾘ ﾔ Ł / TUBE

Package Type	Units	Dimension	(unit mm³)